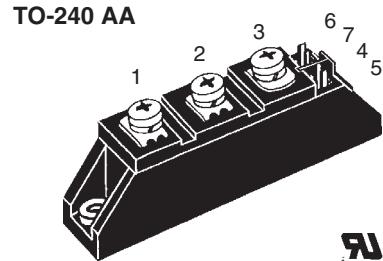


# Thyristor Modules

## Thyristor/Diode Modules

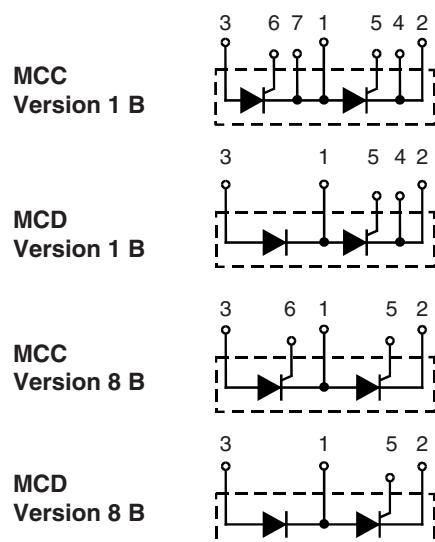
**I<sub>TRMS</sub> = 2x180 A**  
**I<sub>TAVM</sub> = 2x115 A**  
**V<sub>RRM</sub> = 800-1800 V**

V <sub>RSM</sub>	V <sub>RRM</sub>	Type					
V <sub>DSM</sub>	V <sub>DRM</sub>		1 B	8 B	Version	1 B	8 B
900	800	MCC 72-08	io1 B / io8 B		MCC 72-08	io1 B / io8 B	
1300	1200	MCC 72-12	io1 B / io8 B		MCC 72-12	io1 B / io8 B	
1500	1400	MCC 72-14	io1 B / io8 B		MCC 72-14	io1 B / io8 B	
1700	1600	MCC 72-16	io1 B / io8 B		MCC 72-16	io1 B / io8 B	
1900	1800	MCC 72-18	io1 B / io8 B		MCC 72-18	io1 B / io8 B	



Symbol	Conditions	Maximum Ratings		
I <sub>TRMS</sub> , I <sub>FRMS</sub>	T <sub>VJ</sub> = T <sub>VJM</sub>	180	A	
I <sub>TAVM</sub> , I <sub>FAVM</sub>	T <sub>C</sub> = 63°C; 180° sine	115	A	
	T <sub>C</sub> = 85°C; 180° sine	85	A	
I <sub>TSM</sub> , I <sub>FSM</sub>	T <sub>VJ</sub> = 45°C	t = 10 ms (50 Hz), sine	1700	A
	V <sub>R</sub> = 0	t = 8.3 ms (60 Hz), sine	1800	A
	T <sub>VJ</sub> = T <sub>VJM</sub>	t = 10 ms (50 Hz), sine	1540	A
	V <sub>R</sub> = 0	t = 8.3 ms (60 Hz), sine	1640	A
$\int i^2 dt$	T <sub>VJ</sub> = 45°C	t = 10 ms (50 Hz), sine	14 450	A <sup>2</sup> s
	V <sub>R</sub> = 0	t = 8.3 ms (60 Hz), sine	13 500	A <sup>2</sup> s
	T <sub>VJ</sub> = T <sub>VJM</sub>	t = 10 ms (50 Hz), sine	11 850	A <sup>2</sup> s
	V <sub>R</sub> = 0	t = 8.3 ms (60 Hz), sine	11 300	A <sup>2</sup> s
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub>	repetitive, I <sub>T</sub> = 250 A	150	A/μs
	f = 50 Hz; t <sub>p</sub> = 200 μs			
	V <sub>D</sub> = $\frac{2}{3} V_{DRM}$			
	I <sub>G</sub> = 0.45 A	non repetitive, I <sub>T</sub> = I <sub>TAVM</sub>	500	A/μs
	di <sub>G</sub> /dt = 0.45 A/μs			
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> ; R <sub>GR</sub> = $\infty$ ; method 1 (linear voltage rise)	V <sub>DR</sub> = $\frac{2}{3} V_{DRM}$	1000	V/μs
P <sub>GM</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> ; I <sub>T</sub> = I <sub>TAVM</sub>	t <sub>p</sub> = 30 μs	10	W
		t <sub>p</sub> = 300 μs	5	W
P <sub>GAV</sub>			0.5	W
V <sub>RGM</sub>			10	V
T <sub>VJ</sub>			-40...+125	°C
T <sub>VJM</sub>			125	°C
T <sub>stg</sub>			-40...+125	°C
V <sub>ISOL</sub>	50/60 Hz, RMS; I <sub>ISOL</sub> ≤ 1 mA;	t = 1 min	3000	V~
		t = 1 s	3600	V~
M <sub>d</sub>	Mounting torque (M5)		2.5-4.0/22-35	Nm/lb.in.
	Terminal connection torque (M5)		2.5-4.0/22-35	Nm/lb.in.
Weight	Typical including screws		90	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.



### Features

- International standard package, JEDEC TO-240 AA
- Direct copper bonded Al<sub>2</sub>O<sub>3</sub> -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 72873
- Gate-cathode twin pins for version 1B

### Applications

- DC motor control
- Softstart AC motor controller
- Light, heat and temperature control

### Advantages

- Space and weight savings
- Simple mounting with two screws
- Improved temperature and power cycling
- Reduced protection circuits

Symbol	Conditions	Characteristic Values	
$I_{RRM}, I_{DRM}$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	5	mA
$V_T/V_F$	$I_T/I_F = 300 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.74	V
$V_{TO}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )	0.85	V
$r_T$		3.2	$\text{m}\Omega$
$V_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	2.5	V
	$T_{VJ} = -40^\circ\text{C}$	2.6	V
$I_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	150	mA
	$T_{VJ} = -40^\circ\text{C}$	200	mA
$V_{GD}$	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	0.2	V
$I_{GD}$		10	mA
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	450	mA
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200	mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	2	$\mu\text{s}$
$t_q$	$T_{VJ} = T_{VJM}; I_T = 150 \text{ A}, t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = \frac{2}{3} V_{DRM}$	typ. 185	$\mu\text{s}$
$Q_s$	$T_{VJ} = T_{VJM}; I_T/I_F = 50 \text{ A}, -di/dt = 6 \text{ A}/\mu\text{s}$	170	$\mu\text{C}$
$I_{RM}$		45	A
$R_{thJC}$	per thyristor/diode; DC current	0.3	K/W
	per module	0.15	K/W
$R_{thJK}$	per thyristor/diode; DC current	0.5	K/W
	per module	0.25	K/W
$d_s$	Creepage distance on surface	12.7	mm
$d_A$	Strike distance through air	9.6	mm
$a$	Maximum allowable acceleration	50	$\text{m/s}^2$

Optional accessories for module-type MCC 72 version 1 B

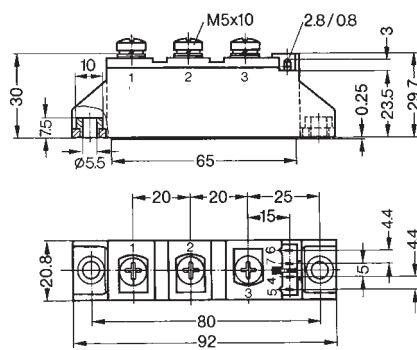
Keyed gate/cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red

Type ZY 200L (L = Left for pin pair 4/5) } UL 758, style 1385,

Type ZY 200R (R = right for pin pair 6/7) } CSA class 5851, guide 460-1-1

#### Dimensions in mm (1 mm = 0.0394")

##### MCC / MCD Version 1 B



##### MCC Version 8 B

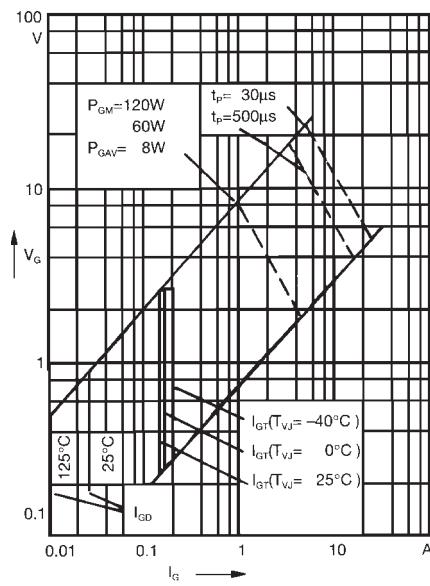
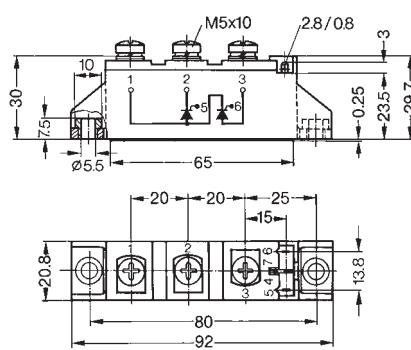


Fig. 1 Gate trigger characteristics

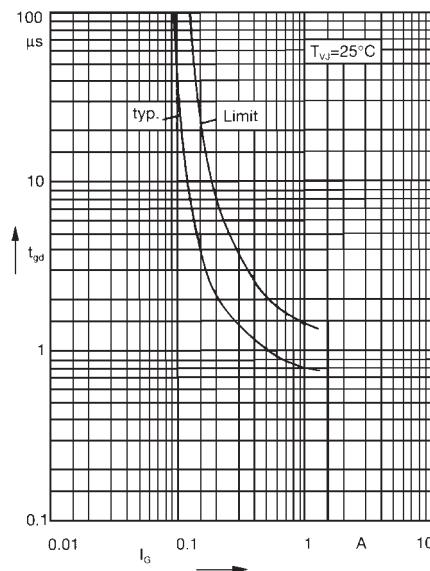
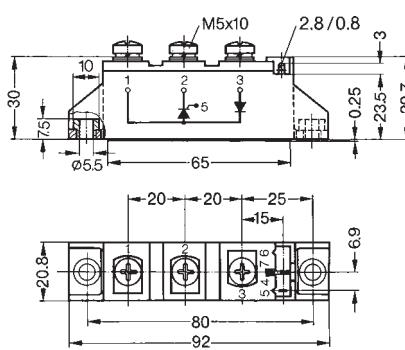


Fig. 2 Gate trigger delay time

##### MCD Version 8 B



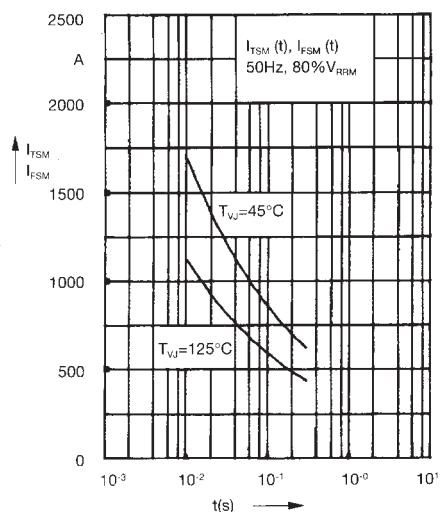


Fig. 3 Surge overload current  
 $I_{TSM}, I_{FSM}$ : Crest value, t: duration

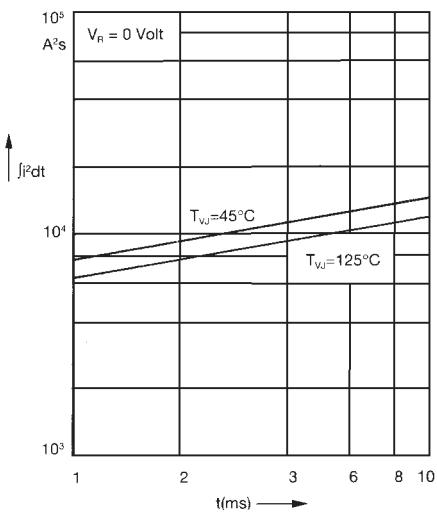


Fig. 4  $j^2dt$  versus time (1-10 ms)

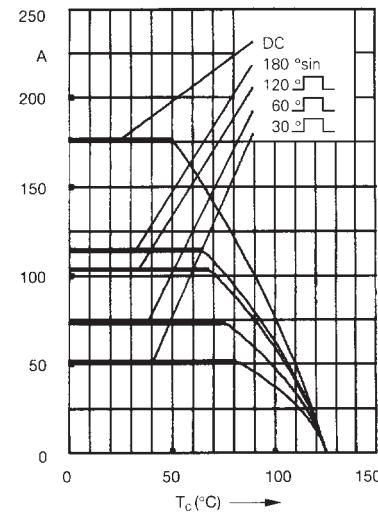


Fig. 4a Maximum forward current at case temperature

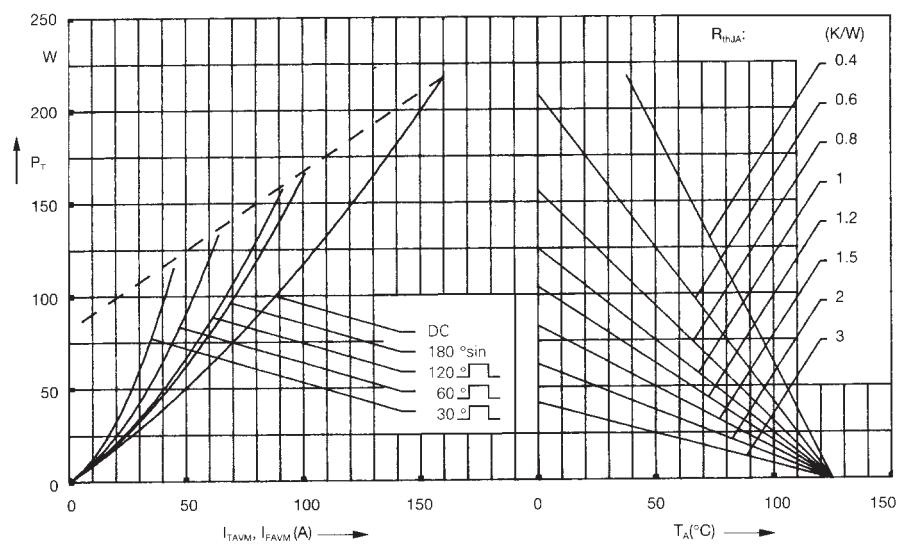


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

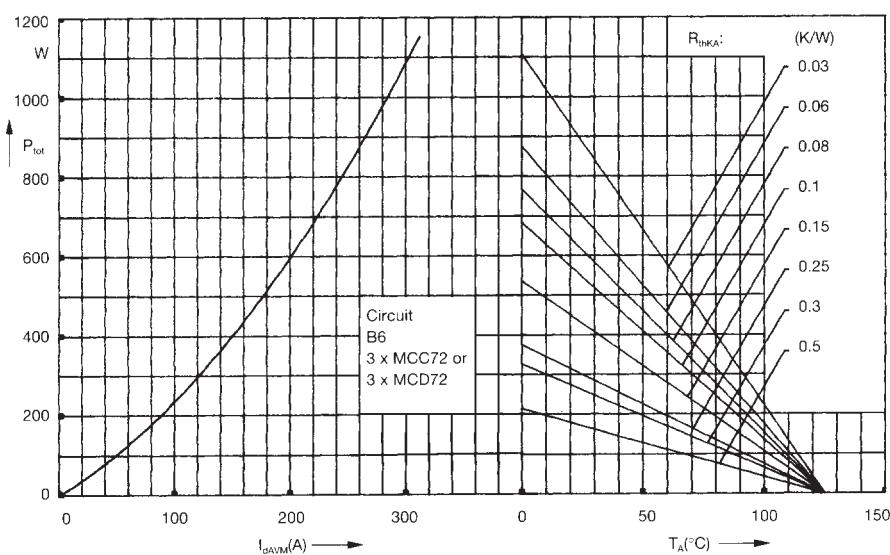
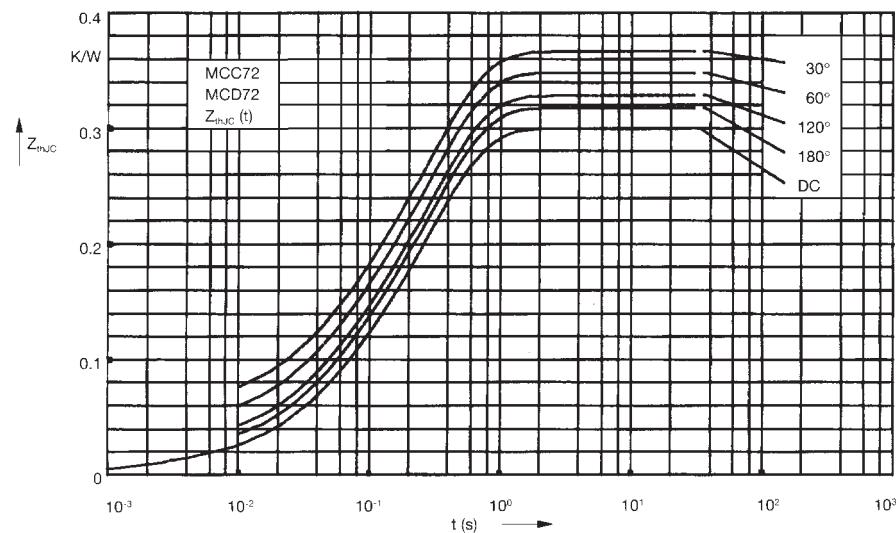
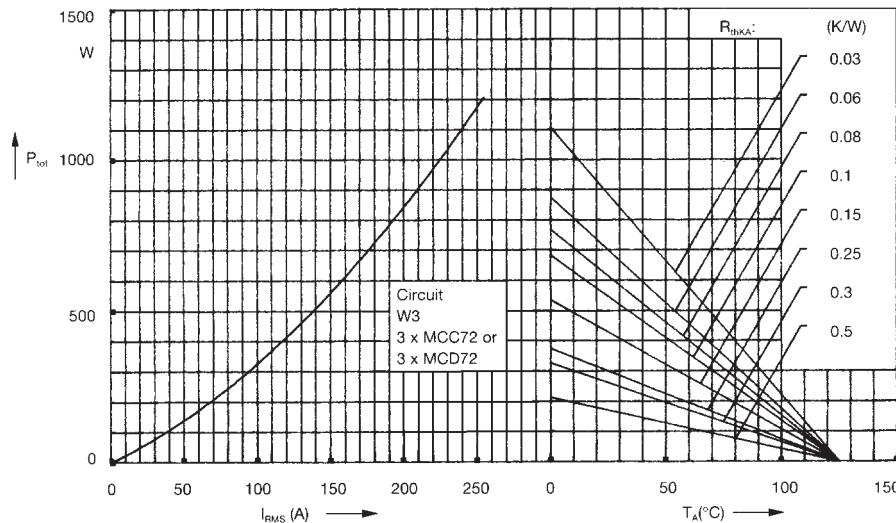


Fig. 6 Three phase rectifier bridge:  
Power dissipation versus direct output current and ambient temperature

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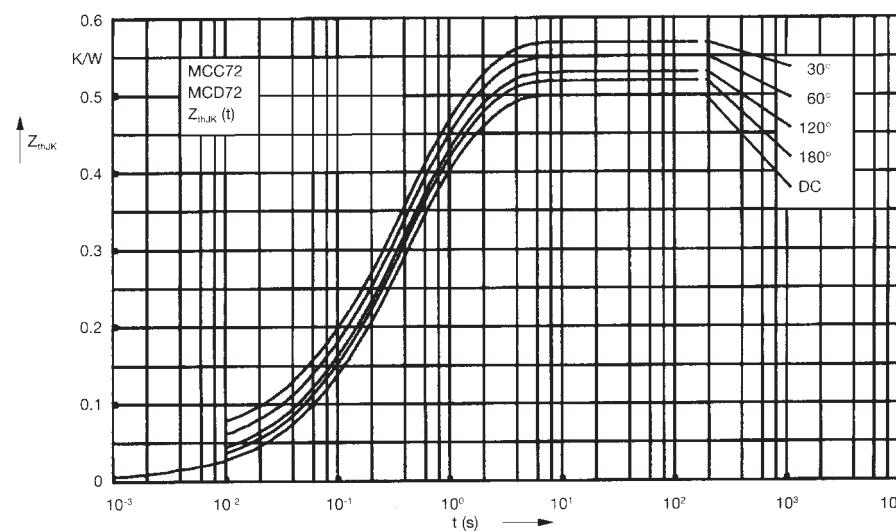


$R_{thJC}$  for various conduction angles d:

d	$R_{thJC}$ (K/W)
DC	0.3
180°	0.31
120°	0.33
60°	0.35
30°	0.37

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.008	0.0019
2	0.054	0.047
3	0.238	0.3



$R_{thJK}$  for various conduction angles d:

d	$R_{thJK}$ (K/W)
DC	0.5
180°	0.51
120°	0.53
60°	0.55
30°	0.57

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.008	0.0019
2	0.054	0.047
3	0.238	0.3
4	0.2	1.25

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[25.330.4753.1](#) [25.330.5253.1](#) [25.334.3253.1](#) [25.334.3353.1](#) [25.350.2053.0](#) [25.352.4753.1](#) [25.522.3253.0](#) [T483C](#) [T484C](#) [T485F](#) [T485H](#)  
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